N-Channel 150-V (D-S) 175 °C MOSFET

PRODUCT SUMMARY		
$V_{(BR)DSS}$ (V)	$r_{DS(on)}$ (Ω)	I_D (A)
150	0.0175 at V_{GS} = 10 V	70

FEATURES

- Trench Power MOSFET
- 175 °C Junction Temperature

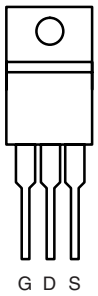
Pb Available

RoHS* COMPLIANT

APPLICATIONS

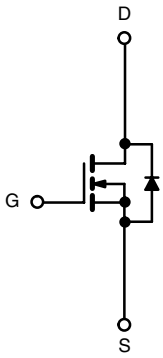
- Primary Side Switch

TO-220AB



Top View

DRAIN connected to TAB



N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS (T_C = 25 °C, unless otherwise noted)				
Parameter		Symbol	Limit	Unit
Drain-Source Voltage		V_{DS}	150	V
Gate-Source Voltage		V_{GS}	± 20	
Continuous Drain Current (T_J = 175 °C)	T_C = 25 °C	I_D	70	A
	T_C = 125 °C		50	
Pulsed Drain Current		I_{DM}	180	
Avalanche Current		I_{AS}	50	
Single Pulse Avalanche Energy[b]	L = 0.1 mH	E_{AS}	125	mJ
Maximum Power Dissipation[b]	T_C = 25 °C	P_D	300[c]	W
	T_A = 25 °C[d]		2.4	
Operating Junction and Storage Temperature Range		T_J, T_{stg}	- 55 to 175	°C

THERMAL RESISTANCE RATINGS			
Parameter	Symbol	Limit	Unit
Junction-to-Ambient-Free Air	R_{thJA}	62.5	°C/W
Junction-to-Case (Drain)	R_{thJC}	0.4	

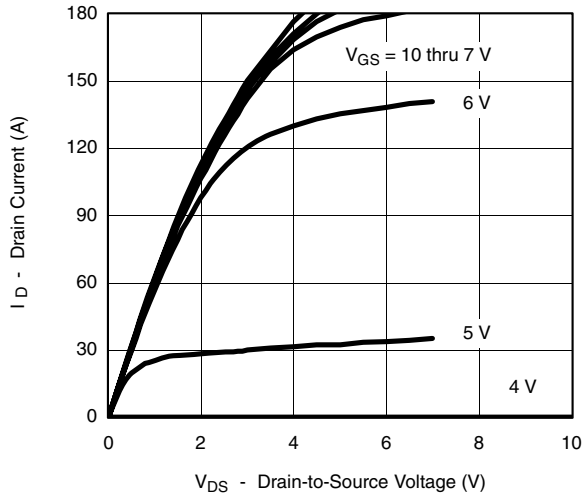
Notes:
a. Package limited.
b. Duty cycle ≤ 1 %.
c. See SOA curve for voltage derating.

SPECIFICATIONS (T_J = 25 °C, unless otherwise noted)						
Parameter	**Symbol**	**Test Conditions**	**Min**	**Typ**	**Max**	**Unit**
Static						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	V_{DS} = 0 V, I_D = 250 µA	150			V
Gate-Threshold Voltage	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = 250 µA	2		4	
Gate-Body Leakage	I_{GSS}	V_{DS} = 0 V, V_{GS} = ± 20 V			± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} = 120 V, V_{GS} = 0 V			1	µA
		V_{DS} = 120 V, V_{GS} = 0 V, T_J = 125 °C			50	
		V_{DS} = 120 V, V_{GS} = 0 V, T_J = 175 °C			250	
On-State Drain Current[a]	$I_{D(on)}$	V_{DS} ≥ 5 V, V_{GS} = 10 V	120			A
Drain-Source On-State Resistance[a]	$r_{DS(on)}$	V_{GS} = 10 V, I_D = 30 A		0.0175		Ω
		V_{GS} = 10 V, I_D = 30 A, T_J = 125 °C		0.042		
		V_{GS} = 10 V, I_D = 30 A, T_J = 175 °C		0.055		
Forward Transconductance[a]	g_{fs}	V_{DS} = 15 V, I_D = 30 A	25			S
Dynamic [b]						
Input Capacitance	C_{iss}	V_{GS} = 0 V, V_{DS} = 25 V, f = 1 MHz		4750		pF
Output Capacitance	C_{oss}			530		
Reverse Transfer Capacitance	C_{rss}			220		
Total Gate Charge[c]	Q_g	V_{DS} = 75 V, V_{GS} = 10 V, I_D = 85 A		76	110	nC
Gate-Source Charge[c]	Q_{gs}			21		
Gate-Drain Charge[c]	Q_{gd}			26		
Turn-On Delay Time[c]	$t_{d(on)}$	V_{DD} = 75 V, R_L = 0.9 Ω I_D ≅ 85 A, V_{GEN} = 10 V, R_G = 2.5 Ω		22	35	ns
Rise Time[c]	t_r			170	250	
Turn-Off Delay Time[c]	$t_{d(off)}$			40	60	
Fall Time[c]	t_f			170	250	
Source-Drain Diode Ratings and Characteristics (T_C = 25 °C)[b]						
Continuous Current	I_S				70	A
Pulsed Current	I_{SM}				180	
Forward Voltage[a]	V_{SD}	I_F = 85 A, V_{GS} = 0 V		1.0	1.5	V
Reverse Recovery Time	t_{rr}	I_F = 50 A, di/dt = 100 A/µs		130	200	ns
Peak Reverse Recovery Current	$I_{RM(REC)}$			8	12	A
Reverse Recovery Charge	Q_{rr}			0.52	1.2	µC

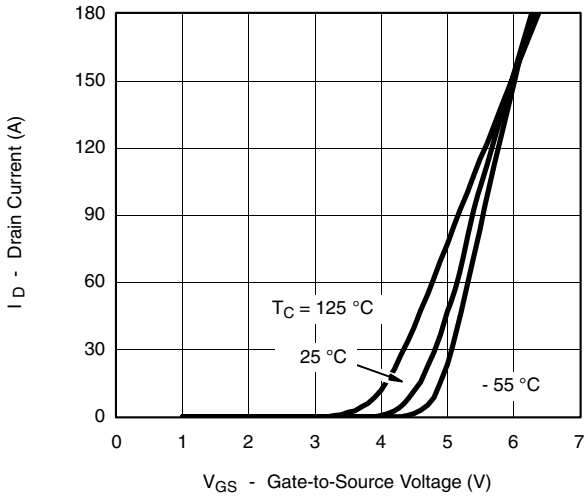
Notes:
a. Pulse test; pulse width ≤ 300 µs, duty cycle ≤ 2 %.
b. Guaranteed by design, not subject to production testing.
c. Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

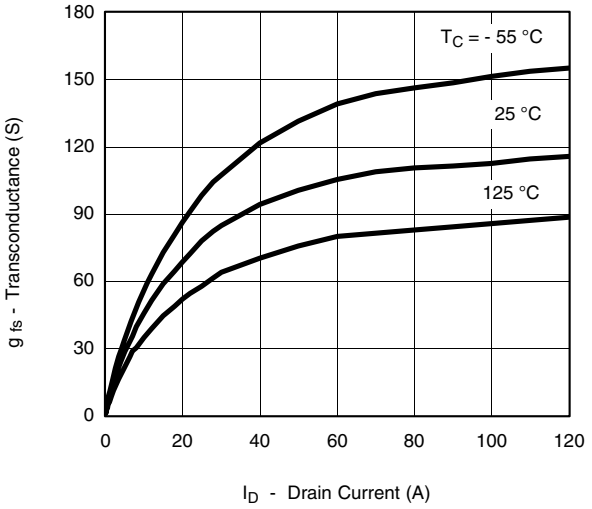
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



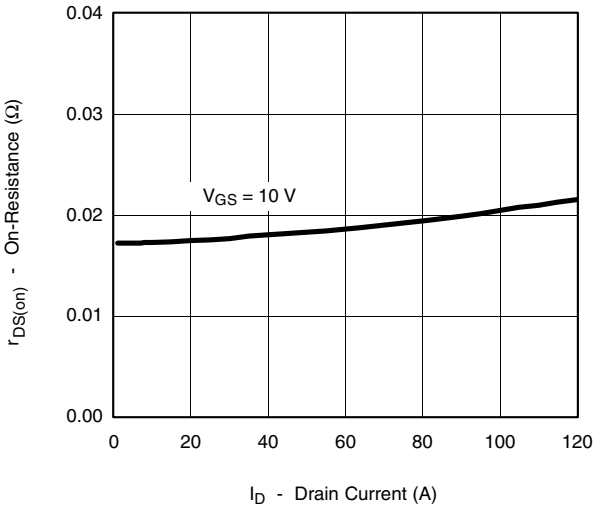
Output Characteristics



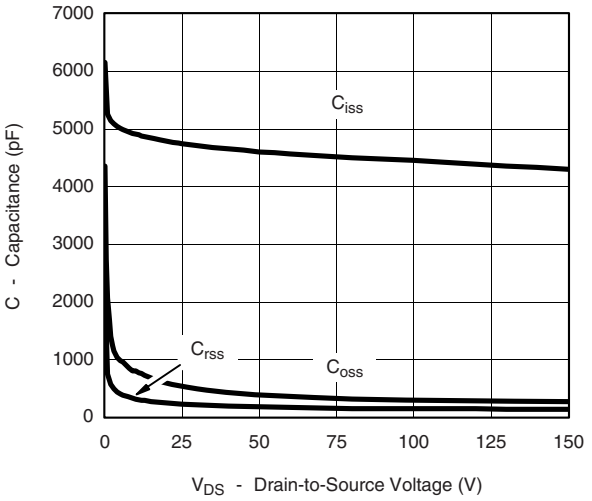
Transfer Characteristics



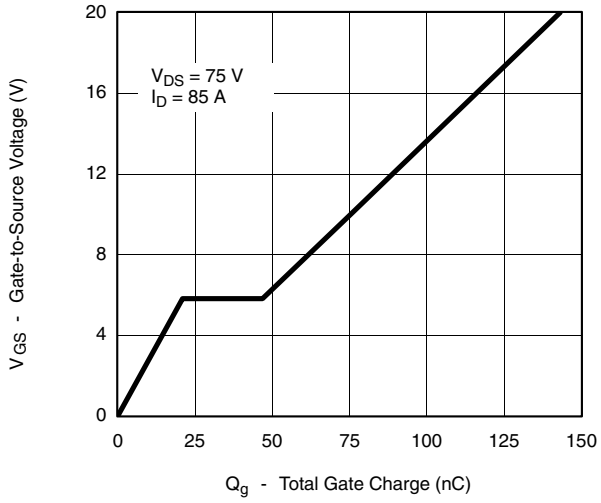
Transconductance



On-Resistance vs. Drain Current

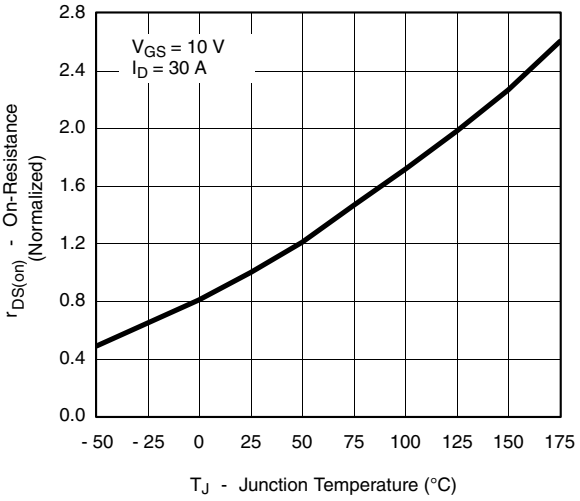


Capacitance

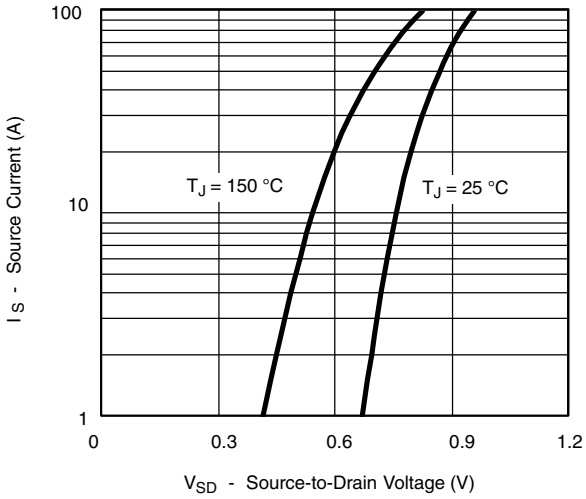


Gate Charge

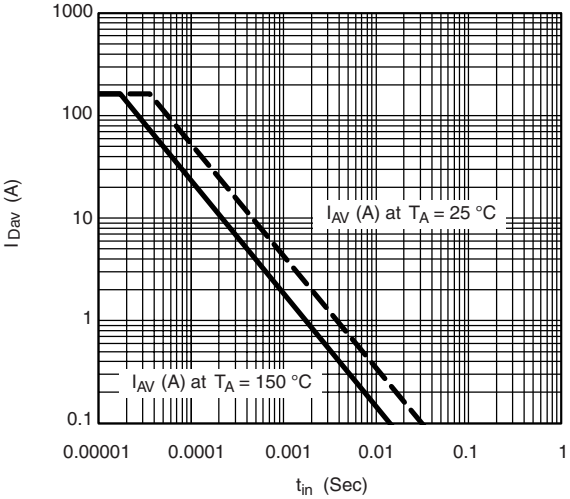
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



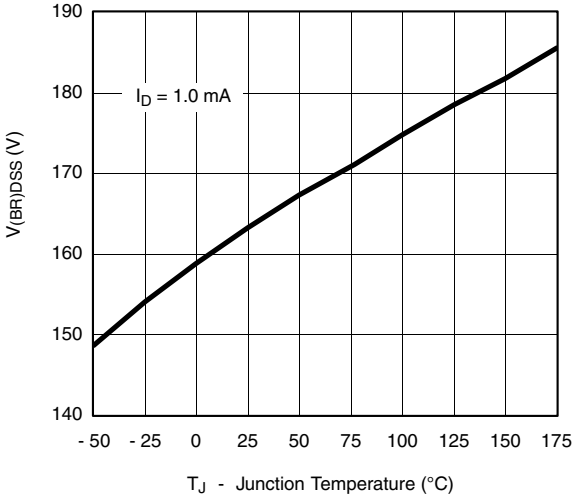
On-Resistance vs. Junction Temperature



Source-Drain Diode Forward Voltage

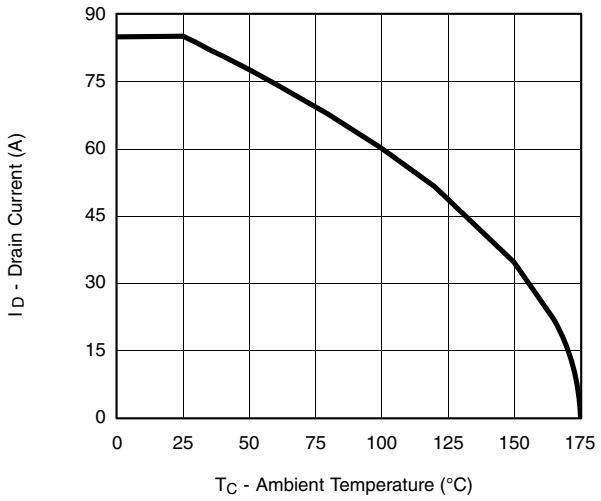


Avalanche Current vs. Time

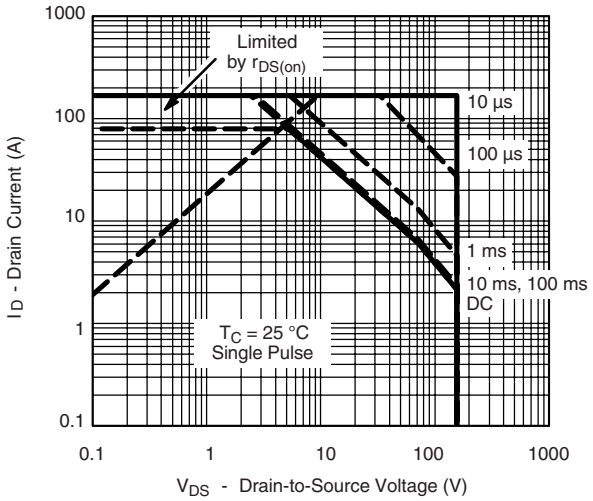


Drain Source Breakdown vs. Junction Temperature

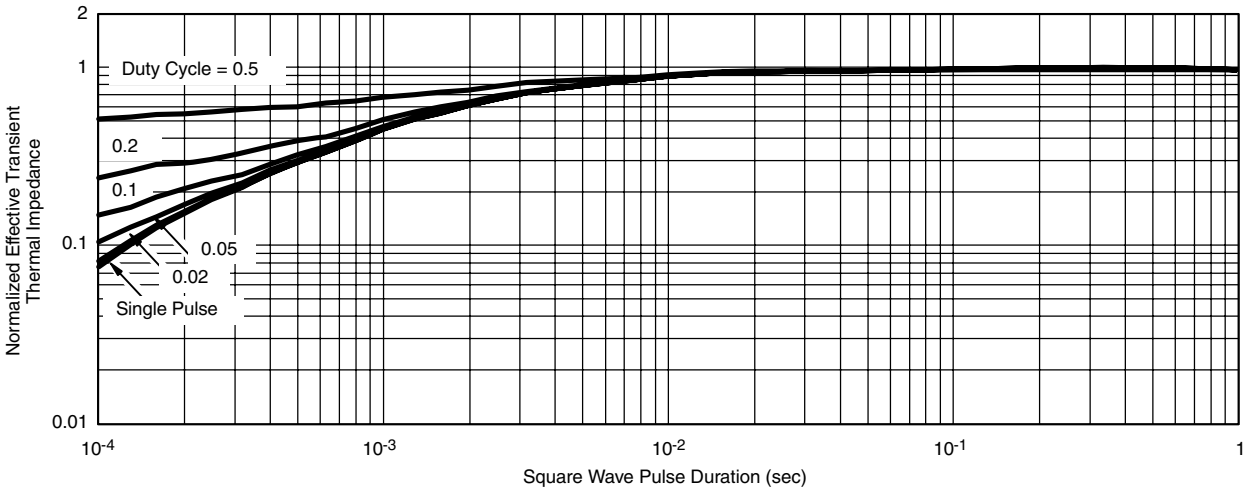
THERMAL RATINGS



Maximum Avalanche and Drain Current vs. Case Temperature



Safe Operating Area



Normalized Thermal Transient Impedance, Junction-to-Case

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